

# Benjamin E Gaddy

## List of Publications by Year in descending order

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11  
papers

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citations

1040056

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1372567

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docs citations

11  
times ranked

1016  
citing authors

#	ARTICLE	IF	CITATIONS
1	Oxygen and silicon point defects in $\text{Al}_x\text{N}_{1-x}$ . Physical Review Materials, 2019, 3, .	2.4	0.65
2	On compensation in Si-doped AlN. Applied Physics Letters, 2018, 112, .	3.3	97
3	Doping and compensation in Al-rich AlGa <sub>N</sub> grown on single crystal AlN and sapphire by MOCVD. Applied Physics Letters, 2018, 112, .	3.3	107
4	Advantages and limitations of UV optoelectronics on AlN substrates. , 2015, , .		0
5	Dysprosium-doped cadmium oxide as a gateway material for mid-infrared plasmonics. Nature Materials, 2015, 14, 414-420.	27.5	216
6	Fermi level control of compensating point defects during metalorganic chemical vapor deposition growth of Si-doped AlGa <sub>N</sub> . Applied Physics Letters, 2014, 105, 222101.	3.3	47
7	The role of the carbon-silicon complex in eliminating deep ultraviolet absorption in AlN. Applied Physics Letters, 2014, 104, .	3.3	59
8	Smooth cubic commensurate oxides on gallium nitride. Journal of Applied Physics, 2014, 115, .	2.5	9
9	Effects of alloying and local order in AuNi contacts for Ohmic radio frequency micro electro mechanical systems switches via multi-scale simulation. Journal of Applied Physics, 2013, 113, 203510.	2.5	2
10	Vacancy compensation and related donor-acceptor pair recombination in bulk AlN. Applied Physics Letters, 2013, 103, .	3.3	80
11	On the origin of the 265-nm absorption band in AlN bulk crystals. Applied Physics Letters, 2012, 100, .	3.3	137